

Specification Amendments

Please amend the paragraph of page 7, lines 3-11 of the specification as follows.

-- Fig. 3 shows XRD results on the Cu₂Se thin film ~~grown which is deposited and formed in step S102 on the InSe film formed in step S101~~. As can be seen, ~~the an~~ initial InSe thin film has been ~~changed to covered by~~ the Cu₂Se thin film. X-ray fluorescence spectroscopy (XRF) analysis confirms that In was not detected and ~~that the second~~ thin film was completely made of Cu₂Se. That is, when Cu was ~~grown deposited~~ on the InSe thin film by MOCVD using a (hfac)Cu(DMB) precursor, ~~original no In has disappeared and was replaced with Cu thus showing conversion InSe layer was detectable. Rather, the XRD analysis showed the presence of Cu thus confirming coverage of the InSe layer into with the layer of Cu_xSe~~. --

Please amend the paragraph of page 7, lines 12-16 of the specification as follows.

-- Fig. 4 shows ~~the~~ XRD results on the CuInSe₂ thin film ~~grown formed by conversion in step S103~~. As can be seen, XRD patterns of the grown CuInSe₂ thin film were consistent with those of a generally known CuInSe₂ single crystal. The ~~grown CuInSe₂~~ thin film was shown to have a single phase of a tetragonal structure. --